

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	NTNS3190NZT5G
Manufacturer:	onsemi
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/onsemi/ntns3190nzt5g.html>

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

NTNS3190NZ

Small Signal MOSFET

20 V, 224 mA, Single N-Channel,
0.62 x 0.62 x 0.4 mm XLLGA3 Package

Features

- Single N-Channel MOSFET
- Ultra Small and Thin Package (0.62 x 0.62 x 0.4 mm)
- Low $R_{DS(on)}$ Solution in 0.62 x 0.62 mm Package
- 1.5 V Gate Voltage Rating
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	224	mA
		$T_A = 85^{\circ}\text{C}$		162	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		241	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	120	mW
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		139	
Pulsed Drain Current		$t_p = 10\text{ }\mu\text{s}$	I_{DM}	673	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	120	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	1040	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5 \text{ s}$ (Note 1)	$R_{\theta JA}$	900	

1. Surface Mounted on FR4 Board using the minimum recommended pad size, (or 2 mm^2), 1 oz Cu.
2. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.



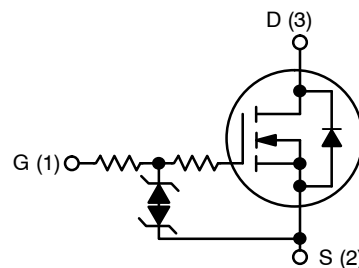
ON Semiconductor®

<http://onsemi.com>

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
20 V	1.4 Ω @ 4.5 V	224 mA
	1.9 Ω @ 2.5 V	
	2.2 Ω @ 1.8 V	
	4.3 Ω @ 1.5 V	

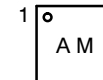
N-Channel MOSFET



MARKING DIAGRAM



XLLGA3
CASE 713AA



A = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTNS3190NZT5G	XLLGA3 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTNS3190NZ

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = -250 μA, ref to 25°C		19		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V			1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8.0 V			±2.0	μA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.4		1.0	V
Negative Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			1.9		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 100 mA		0.65	1.4	Ω
		V _{GS} = 2.5 V, I _D = 50 mA		0.9	1.9	
		V _{GS} = 1.8 V, I _D = 20 mA		1.1	2.2	
		V _{GS} = 1.5 V, I _D = 10 mA		1.4	4.3	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 100 mA		0.56		S
Source-Drain Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 mA		0.55	1.0	V

CHARGES & CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		15.8		pF
Output Capacitance	C _{OSS}			3.5		
Reverse Transfer Capacitance	C _{RSS}			2.4		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 200 mA		0.70		nC
Threshold Gate Charge	Q _{G(TH)}			0.05		
Gate-to-Source Charge	Q _{GS}			0.14		
Gate-to-Drain Charge	Q _{GD}			0.10		

SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 15 V, I _D = 200 mA, R _G = 2 Ω		18		ns
Rise Time	t _r			35		
Turn-Off Delay Time	t _{d(OFF)}			201		
Fall Time	t _f			110		

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

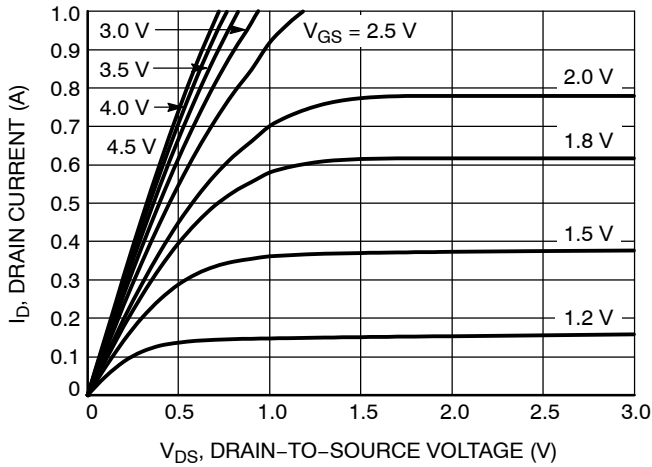


Figure 1. On-Region Characteristics

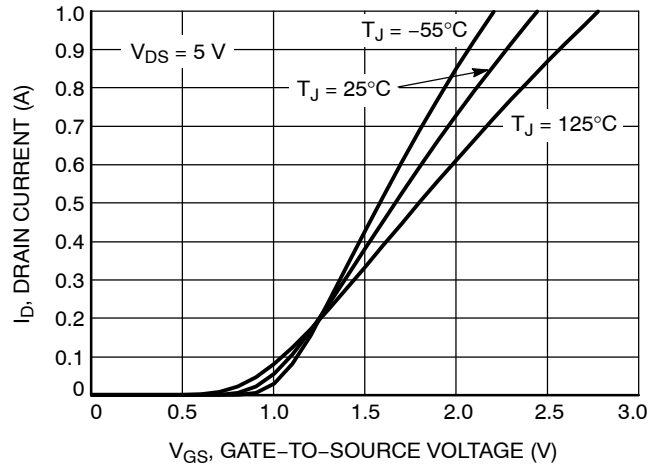


Figure 2. Transfer Characteristics

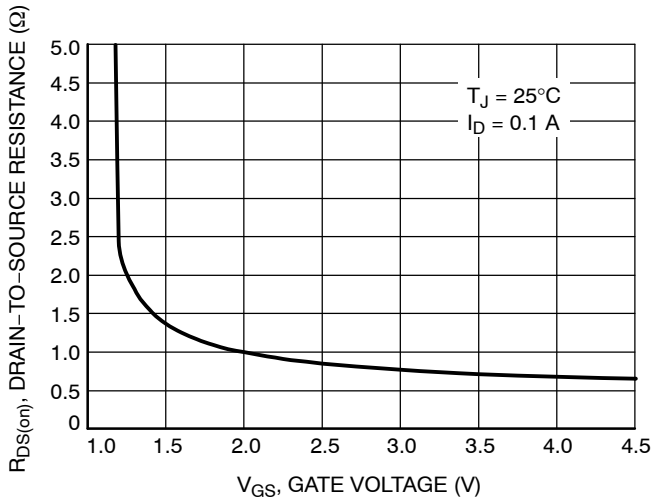


Figure 3. On-Resistance vs. Gate-to-Source Voltage

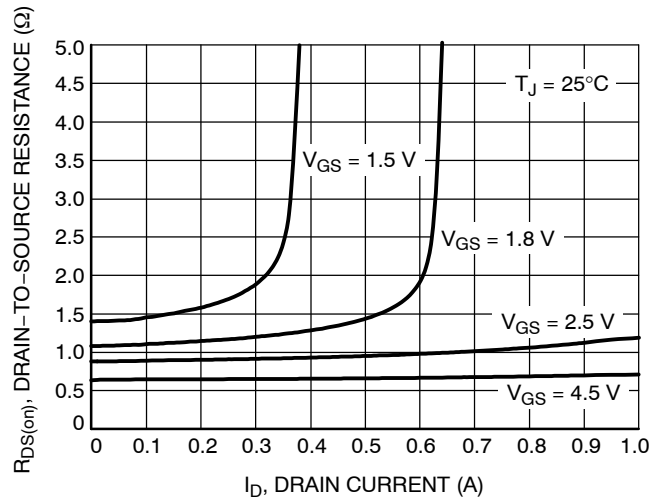


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

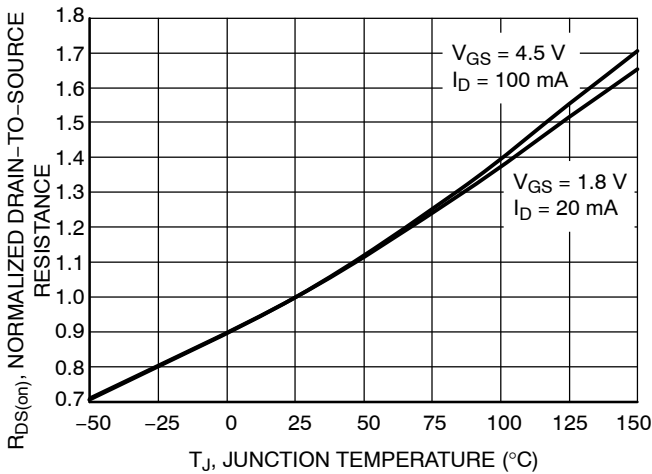


Figure 5. On-Resistance Variation with Temperature

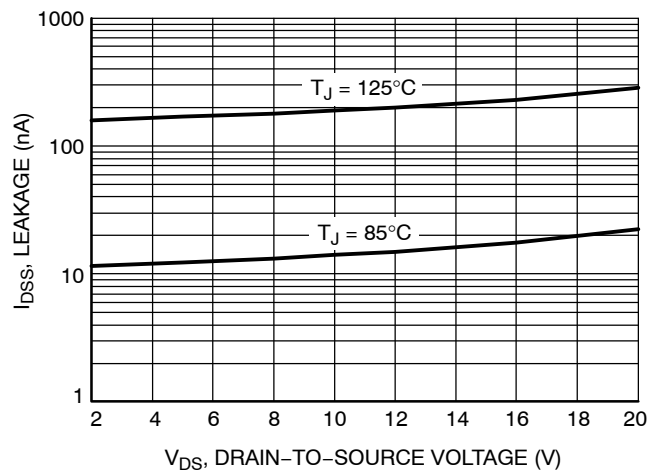


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

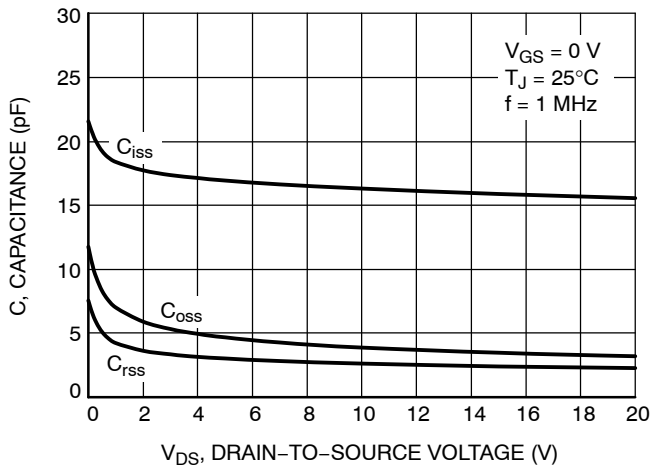


Figure 7. Capacitance Variation

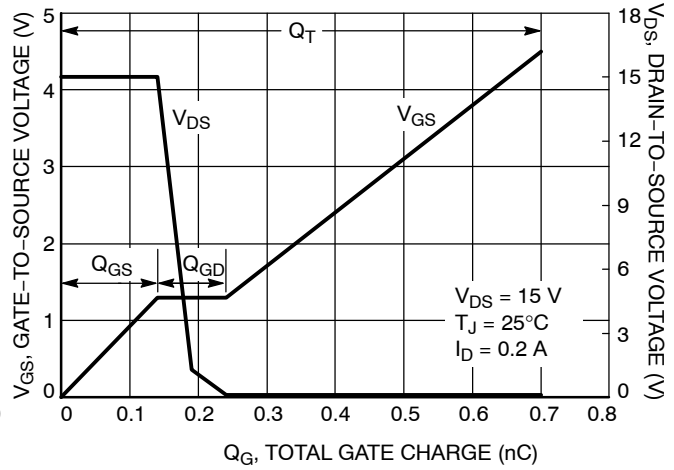


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

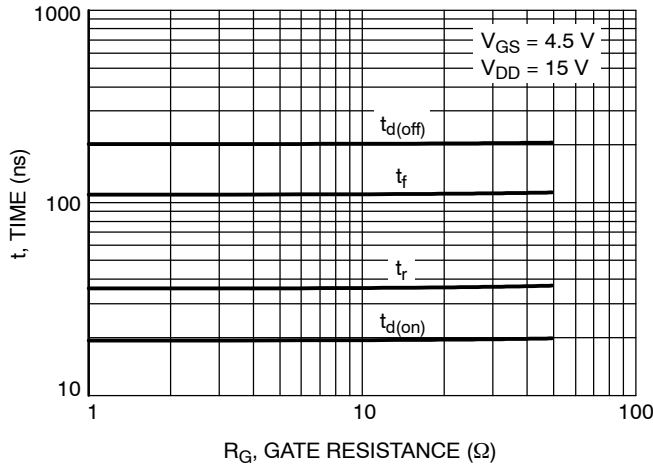


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

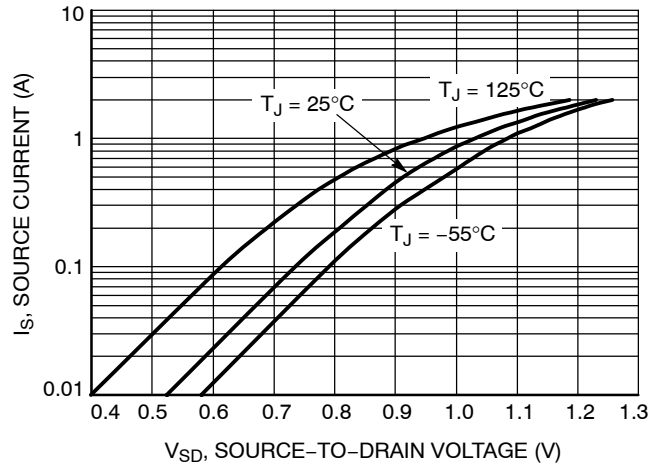


Figure 10. Diode Forward Voltage vs. Current

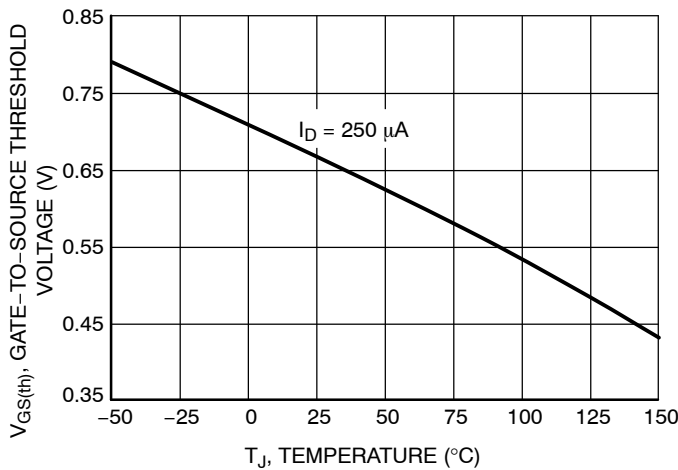


Figure 11. Threshold Voltage

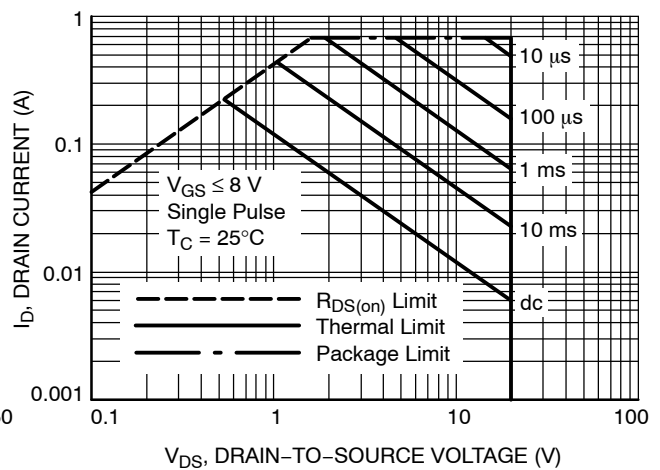


Figure 12. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

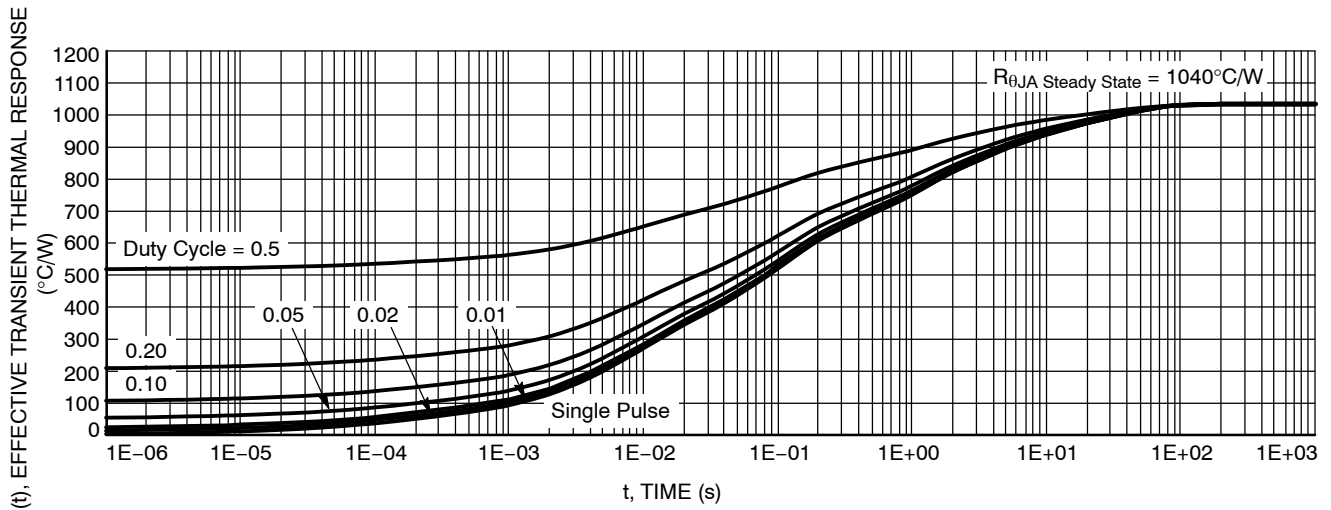
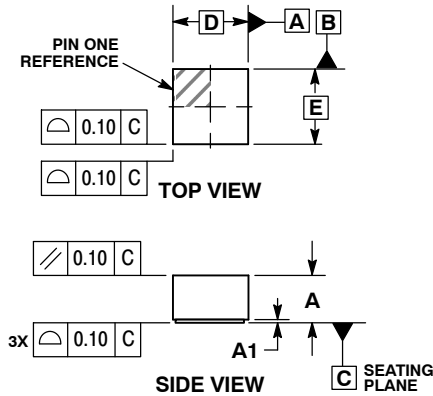


Figure 13. FET Thermal Response

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PACKAGE DIMENSIONS

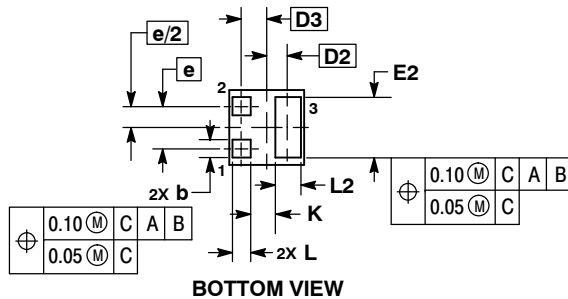
XLLGA3, 0.62x0.62, 0.35P
CASE 713AA
ISSUE B



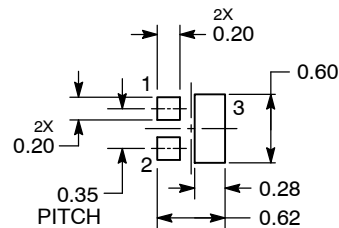
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.100	0.200
D	0.620	BSC
D2	0.175	BSC
D3	0.205	BSC
E	0.620	BSC
E2	0.400	0.600
e	0.350	BSC
K	0.200	REF
L	0.090	0.210
L2	0.110	0.310



MINIMUM RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*Additional information concerning board mounting for this package may be found in Document AND9099/D, "Board Level Application Note for XLLGA 3-Lead 0.62x0.62 Package". For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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